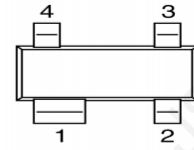
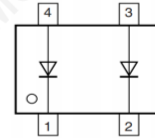


Features and benefits

- ◆ High switching speed: t_{rr} 4 ns
- ◆ Reverse voltage: V_R 75 V
- ◆ Repetitive peak reverse voltage: V_{RRM} 85 V
- ◆ Repetitive peak forward current: I_{FRM} 500 mA
- ◆ small SMD package



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Applications

- ◆ High-speed switching in e.g. surface-mounted circuits

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Peak Reverse Voltage	V_{RM}	100	V
Reverse Voltage	V_R	80	V
Average Rectified Forward Current	$I_{F(AV)}$	215	mA
Forward Continuous Current	I_{FM}	500	mA
Non-Repetitive Peak Forward Surge Current (at $t = 1 \mu\text{s}$)	I_{FSM}	4	A
Power Dissipation	P_d	400	mW
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 65 to + 150	$^\circ\text{C}$

Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Min.	Max.	Unit
Forward Voltage at $I_F = 5 \text{ mA}$ at $I_F = 10 \text{ mA}$ at $I_F = 100 \text{ mA}$ at $I_F = 150 \text{ mA}$	V_F	0.62 - - -	0.72 0.855 1 1.25	V
Reverse Leakage Current at $V_R = 80 \text{ V}$ at $V_R = 20 \text{ V}$ at $V_R = 75 \text{ V}, T_J = 150^\circ\text{C}$ at $V_R = 25 \text{ V}, T_J = 150^\circ\text{C}$	I_R	- - - -	1000 30 50 30	nA nA μA μA
Reverse Breakdown Voltage at $I_R = 100 \mu\text{A}$	$V_{(BR)R}$	80	-	V
Total Capacitance at $V_R = 0.5 \text{ V}, f = 1 \text{ MHz}$	C_{tot}	-	4	pF
Reverse Recovery Time at $I_F = I_R = 10 \text{ mA}, I_{rr} = 0.1 \times I_R, R_L = 100 \Omega$	t_{rr}	-	4	ns

RATING AND CHARACTERISTIC CURVES (BAS28)

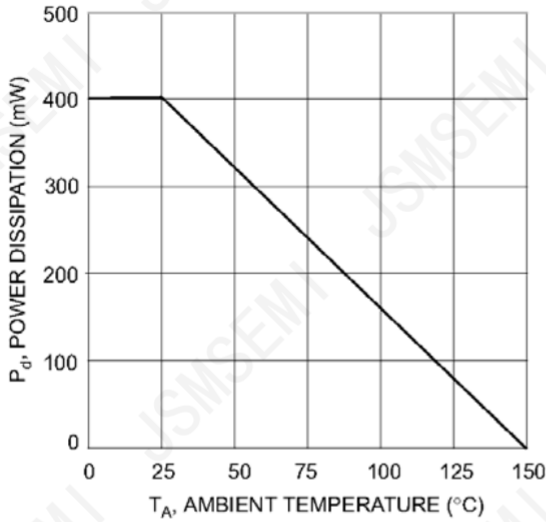


Fig. 1 Power Derating Curve

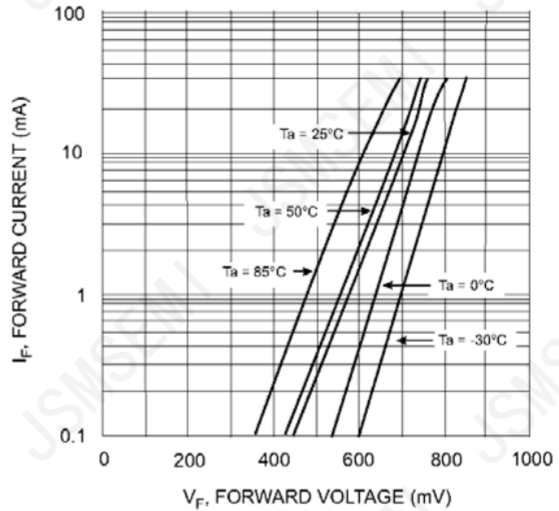


Fig. 2 Typical Forward Characteristics

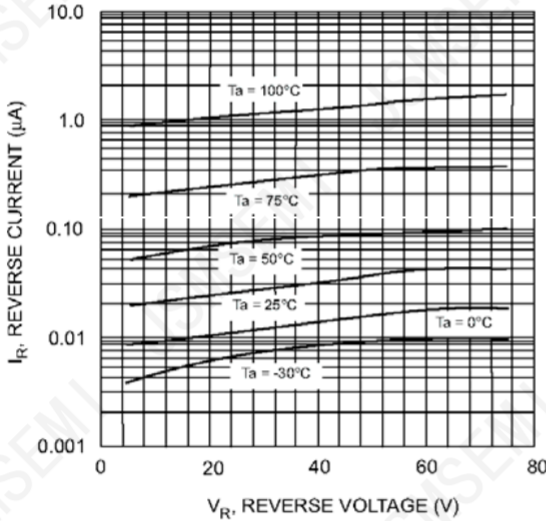


Fig. 3 Typical Reverse Characteristics

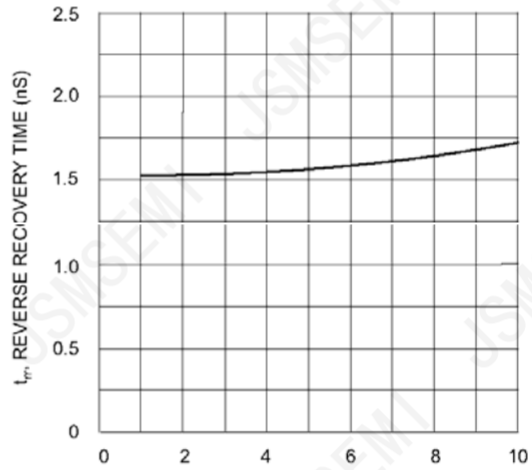


Fig. 4 Reverse Recovery Time vs. Forward Current

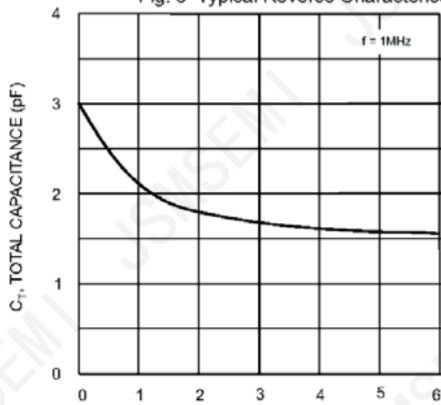
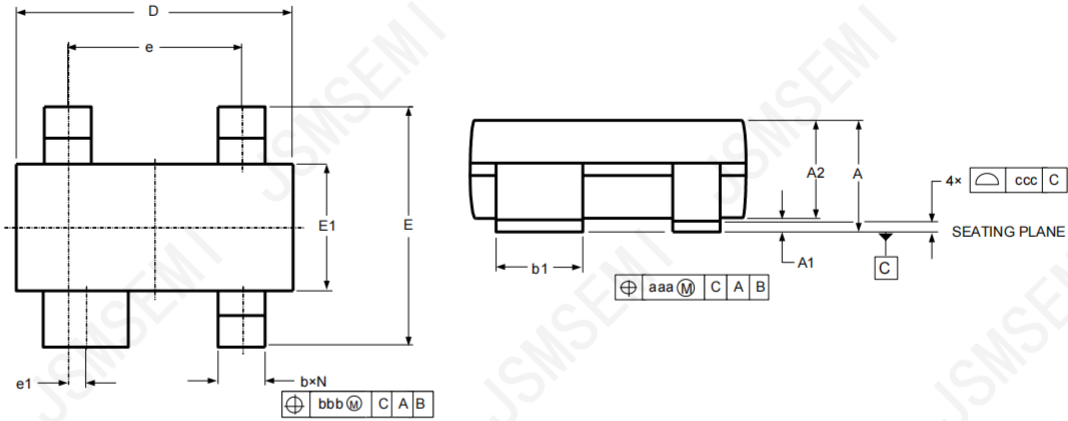


Fig. 5 Total Capacitance vs. Reverse Voltage

SOT-143



DIMENSIONS				
SYMBOL	MILLIMETER		INCHES	
	MIN	MAX	MIN	MAX
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
b1	0.750	0.900	0.030	0.035
D	2.800	3.000	0.110	0.118
e	1.800	2.000	0.071	0.079
e1	0.200TYP		0.008TYP	
E	2.250	2.550	0.089	0.100
E1	1.200	1.400	0.047	0.055
θ	0°	8°	0°	8°
aaa	.006		0.15	
bbb	.008		0.20	
ccc	.004		0.10	

Dimensions in inches and (millimeters)

Revision History

Rev.	Change	Date
V1.0	Initial version	2/23/2024

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